

isc Silicon NPN Power Transistor

BUT12A

DESCRIPTION

- High Voltage
- High Speed Switching

APPLICATIONS

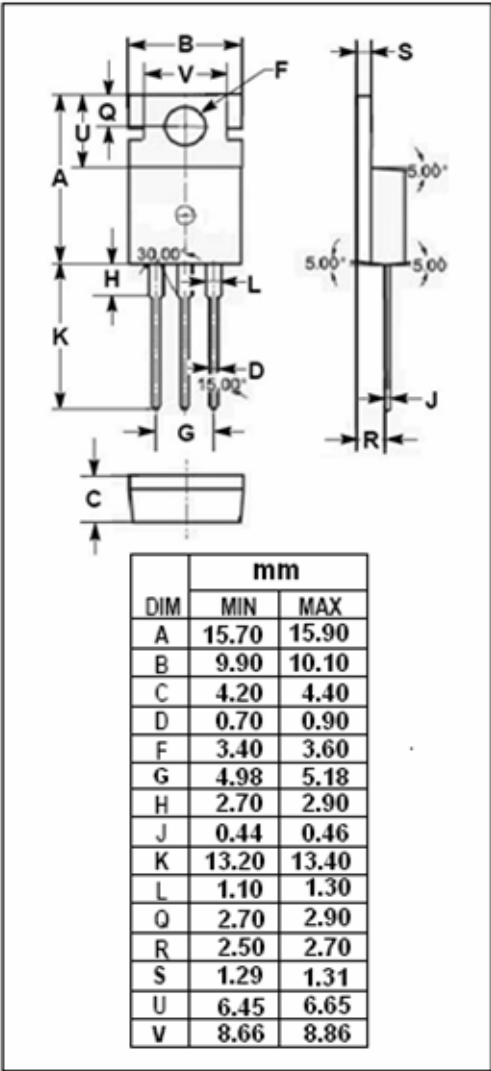
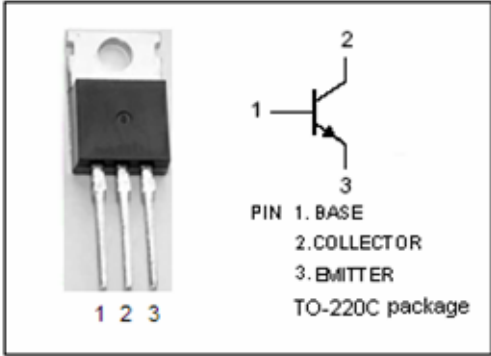
- Converters
- Inverters
- Switching regulators
- Motor control systems

ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	1000	V
V _{CEO}	Collector-Emitter Voltage	450	V
V _{EBO}	Emitter-Base Voltage	9	V
I _C	Collector Current-Continuous	8	A
I _{CM}	Collector Current-Peak	20	A
I _B	Base Current-Continuous	4	A
I _{BM}	Base Current-Peak	6	A
P _C	Collector Power Dissipation @T _C =25°C	125	W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-65~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	1.0	°C/W



ISC Silicon NPN Power Transistor**BUT12A****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 0.1A; I _B = 0, L= 25mH	450			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 1A			1.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 5A; I _B = 1A			1.5	V
I _{CES}	Collector Cutoff Current	V _{CE} =RatedV _{CES} ; V _{BE} = 0 V _{CE} =RatedV _{CES} ; V _{BE} = 0; T _C =125°C			1 3	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 9V; I _C = 0			10	mA
h _{FE-1}	DC Current Gain	I _C = 10mA; V _{CE} = 5V	10		35	
h _{FE-2}	DC Current Gain	I _C = 1A; V _{CE} = 5V	10		35	

Switching Times ;Resistive Load

t _{on}	Turn-on Time	I _C = 5A; I _{B1} = -I _{B2} =1A			1.0	μ s
t _s	Storage Time				4.0	μ s
t _f	Fall Time				0.8	μ s